



LOW POWER NPN SILICON TRANSISTOR

Qualified per MIL-PRF-19500/391

Qualified Levels:
JAN, JANTX,
JANTXV, and JANS

DESCRIPTION

This 2N3019 NPN leaded silicon transistor device is military qualified for high-reliability applications. Microsemi also offers numerous other transistor products to meet higher and lower power ratings with various switching speed requirements in both through-hole and surface-mount packages.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- JEDEC registered 2N3019 number.
- JAN, JANTX, JANTXV and JANS qualifications are available per MIL-PRF-19500/391.
- Rad hard levels are also available per MIL-PRF-19500/391. (For RHA datasheet see [JANS D2N3019](#).)
- RoHS compliant by design.

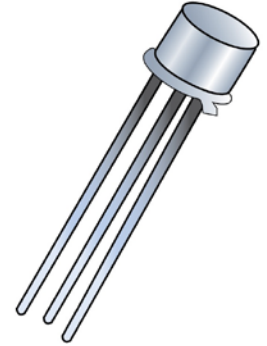
APPLICATIONS / BENEFITS

- Long leaded TO-5 package.
- Lightweight.
- Low power.
- Military and other high-reliability applications.

MAXIMUM RATINGS @ T_A = +25 °C unless otherwise noted


Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T _J and T _{STG}	-65 to +200	°C
Thermal Resistance Junction-to-Ambient	R _{θJA}	195	°C/W
Thermal Resistance Junction-to-Case	R _{θJC}	30	°C/W
Collector-Emitter Voltage	V _{CEO}	80	V
Collector-Base Voltage	V _{CBO}	140	V
Emitter-Base Voltage	V _{EBO}	7.0	V
Collector Current	I _C	1.0	A
Total Power Dissipation:			
@ T _A = +25 °C ⁽¹⁾	P _D	0.8	W
@ T _C = +25 °C ⁽²⁾		5.0	


- Notes:**
1. Derate linearly 4.6 mW/°C for T_A ≥ +25 °C.
 2. Derate linearly 28.6 mW/°C for T_C ≥ +25 °C.





TO-5 Package

Also available in:

TO-39 (TO-205AD)
(short-leaded)
 [2N3019S](#)

TO-46 (TO-206AB)
(leaded)
 [2N3057A](#)

TO-18 (TO-206AA)
(leaded)
 [2N3700](#)

UB package
(leaded)
 [2N3700UB](#)

MSC – Lawrence

6 Lake Street,
Lawrence, MA 01841
Tel: 1-800-446-1158 or
(978) 620-2600
Fax: (978) 689-0803

MSC – Ireland

Gort Road Business Park,
Ennis, Co. Clare, Ireland
Tel: +353 (0) 65 6840044
Fax: +353 (0) 65 6822298

Website:

www.microsemi.com

MECHANICAL and PACKAGING

- CASE: Hermetically sealed, kovar base, nickel cap.
- TERMINALS: Gold plate, solder dip (Sn63/Pb37) available upon request. NOTE: Solder dip will eliminate RoHS compliance.
- MARKING: Part number, date code, manufacturer's ID and serial number.
- POLARITY: NPN.
- WEIGHT: Approximately 1.064 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

JAN 2N3019

Reliability Level

JAN = JAN level
 JANTX = JANTX level
 JANTXV = JANTXV level
 JANS = JANS level
 Blank = Commercial

JEDEC type number

(see [Electrical Characteristics](#) table)

SYMBOLS & DEFINITIONS

Symbol	Definition
f	Frequency
I_B	Base current (dc)
I_E	Emitter current (dc)
T_A	Ambient temperature
T_C	Case temperature
V_{CB}	Collector to base voltage (dc)
V_{CE}	Collector to emitter voltage (dc)
V_{EB}	Emitter to base voltage (dc)

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$, unless otherwise noted

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Current $I_C = 30\text{ mA}$	$V_{(BR)CEO}$	80		V
Collector-Base Cutoff Current $V_{CB} = 140\text{ V}$	I_{CBO}		10	μA
Emitter-Base Cutoff Current $V_{EB} = 7\text{ V}$	I_{EBO1}		10	μA
Collector-Emitter Cutoff Current $V_{CE} = 90\text{ V}$	I_{CES}		10	ηA
Emitter-Base Cutoff Current $V_{EB} = 5.0\text{ V}$	I_{EBO2}		10	ηA
ON CHARACTERISTICS				
Forward-Current Transfer Ratio $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 0.1\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 1.0\text{ A}, V_{CE} = 10\text{ V}$	h_{FE}	100 50 90 50 15	300 300 300	
Collector-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 500\text{ mA}, I_B = 50\text{ mA}$	$V_{CE(sat)}$		0.2 0.5	V
Base-Emitter Saturation Voltage $I_C = 150\text{ mA}, I_B = 15\text{ mA}$	$V_{BE(sat)}$		1.1	V

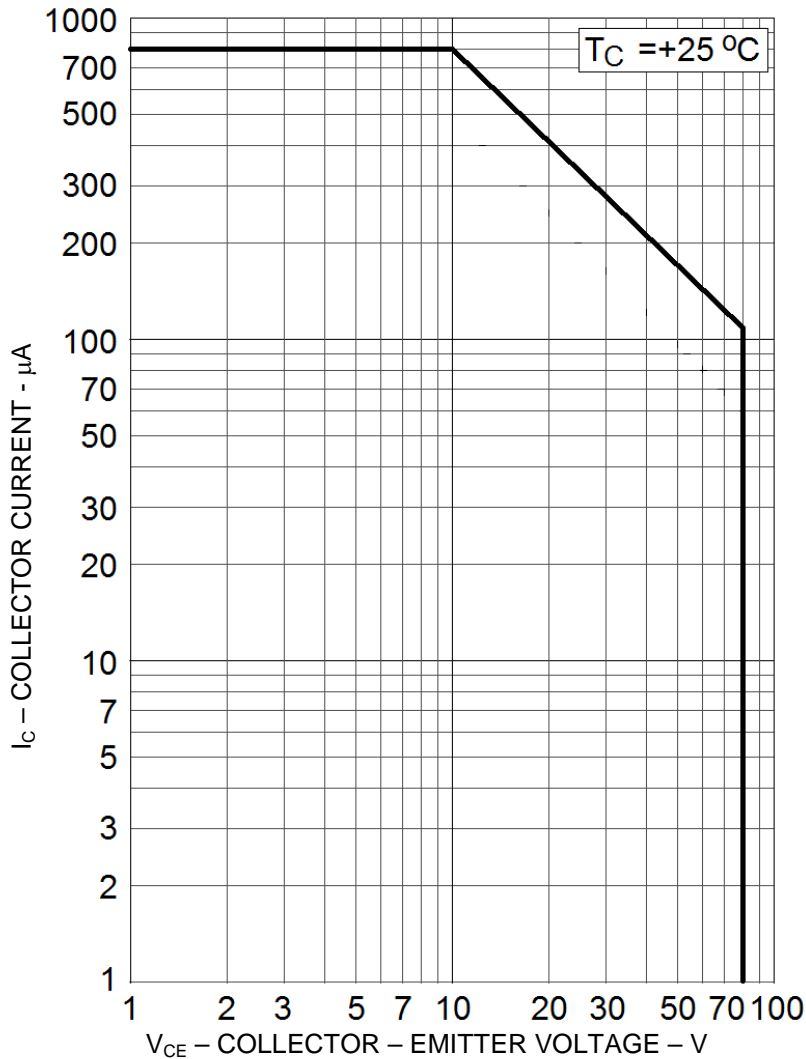
DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 1.0\text{ mA}, V_{CE} = 5.0\text{ V}, f = 1.0\text{ kHz}$	h_{fe}	80	400	
Magnitude of Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 50\text{ mA}, V_{CE} = 10\text{ V}, f = 20\text{ MHz}$	$ h_{fe} $	5.0	20	
Output Capacitance $V_{CB} = 10\text{ V}, I_E = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{obo}		12	pF
Input Capacitance $V_{EB} = 0.5\text{ V}, I_C = 0, 100\text{ kHz} \leq f \leq 1.0\text{ MHz}$	C_{ibo}		60	pF

ELECTRICAL CHARACTERISTICS @ $T_A = +25\text{ }^\circ\text{C}$, unless otherwise noted (continued)
SAFE OPERATION AREA (See SOA graph below and [MIL-STD-750, method 3053](#))

DC Tests
 $T_C = 25\text{ }^\circ\text{C}$, 1 cycle, $t = 10\text{ ms}$

Test 1	$V_{CE} = 10\text{ V}$ $I_C = 500\text{ mA}$
Test 2	$V_{CE} = 40\text{ V}$ $I_C = 125\text{ mA}$
Test 3	$V_{CE} = 80\text{ V}$ $I_C = 60\text{ mA}$

 (1) Pulse Test: Pulse Width = $300\text{ }\mu\text{s}$, duty cycle $\leq 2.0\%$.

Maximum Safe Operating Area

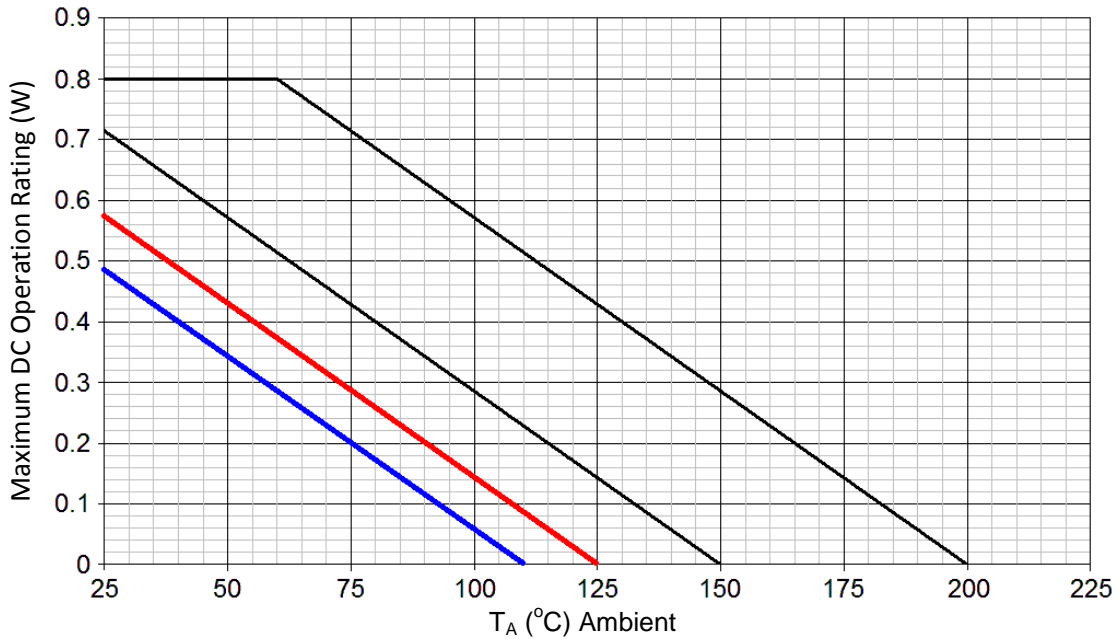
GRAPHS


FIGURE 1
Temperature – Power Derating ($R_{\theta JA}$)

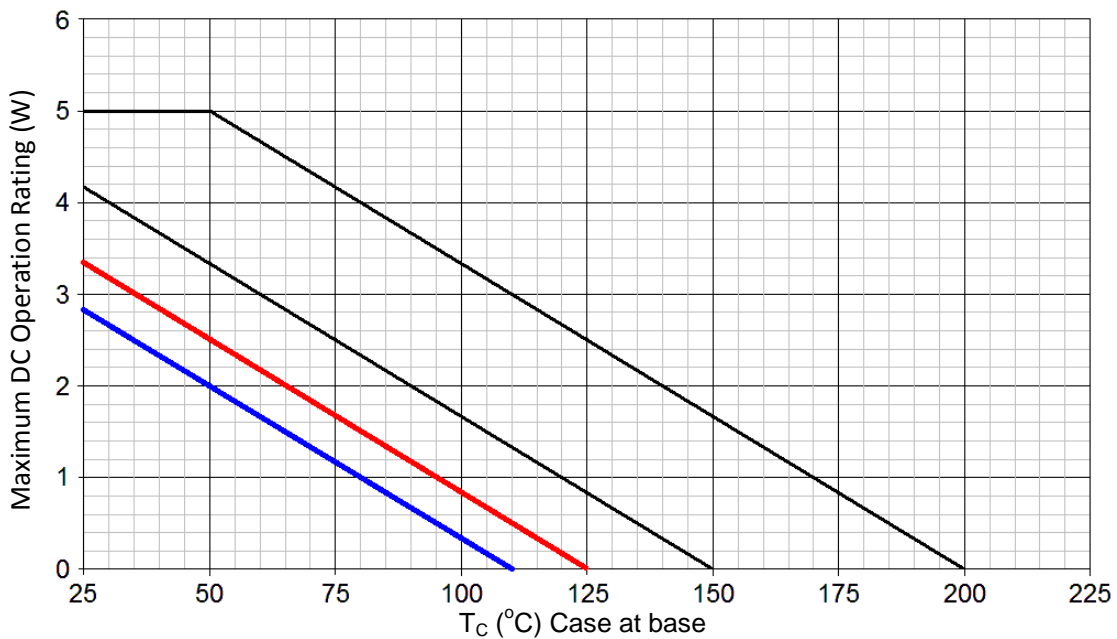
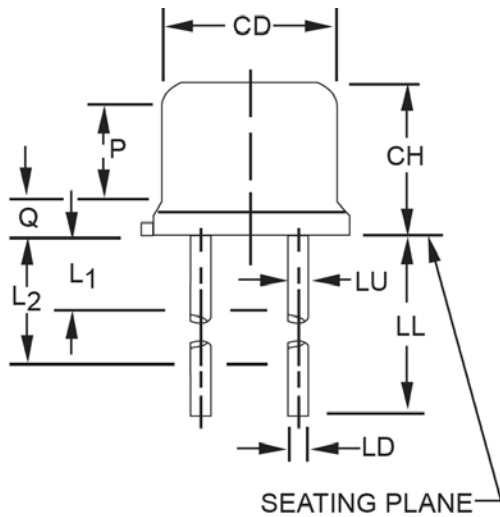
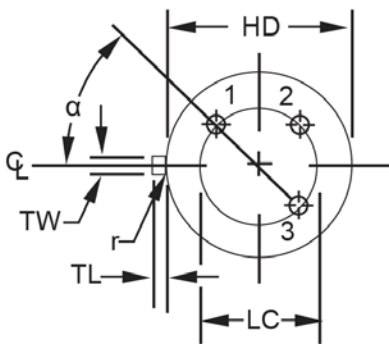


FIGURE 2
Temperature – Power Derating ($R_{\theta JC}$)

PACKAGE DIMENSIONS


Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		6
LD	.016	.021	0.41	0.53	7, 8
LL	1.500	1.750	38.10	44.45	7, 8
LU	.016	.019	0.41	0.48	7, 8
L₁		.050		1.27	7, 8
L₂	.250		6.35		7, 8
Q		.050		1.27	5
TL	.029	.045	0.74	1.14	4
TW	.028	.034	0.71	0.86	3
r		.010		0.25	10
α	45° TP		45° TP		6
P	.100	-	2.54	-	


NOTES:

- Dimensions are in inches.
- Millimeters are given for general information only.
- Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
- Dimension TL measured from maximum HD.
- Body contour optional within zone defined by HD, CD, and Q.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. This device may be measured by direct methods.
- Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
- All three leads.
- The collector shall be internally connected to the case.
- Dimension r (radius) applies to both inside corners of tab.
- In accordance with ASME Y14.5M, diameters are equivalent to Φx symbology.
- Lead 1 = emitter, lead 2 = base, lead 3 = collector.

Данный компонент на территории Российской Федерации

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9